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Substitute for form 1449A/PTO INFORMATION DISCLOSURE STATEMENT BY APPLICANT <i>(use as many sheets as necessary)</i>				Complete if Known	
Application Number		Based on SN 10/035,441			
Filing Date		Filed: January 4, 2002			
First Named Inventor		Naoaki YAMAGUCHI et al.			
Group Art Unit		1765			
Examiner Name		Anita Karen Alanko			
Attorney Docket Number		0756-7191			
Sheet	3	of	3		

U.S. PATENT DOCUMENTS						
Examiner Initials ¹	Cite No. ¹	U.S. Patent Document		Name of Patentee or Applicant of Cited Document	Date of Publication of Cited Document MM-DD-YYYY	Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear
		Number	Kind Code ² (if known)			
CL		5,472,505		Lee et al.	12/05/1995	_____
CL		5,294,518		Brady et al.	03/15/1994	_____
CL		5,240,581		Kim	08/31/1993	_____

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CL		G. Liu, S.J. Fonash, "Polycrystalline Silicon Thin Film Transistors on Corning 7059 Glass Substrates Using Short Time, Low Temperature Processing," Appl. Phys. Lett 62 (20), May 17, 1993, 1993 American Institute of Physics, pp. 2554-2556.	
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Examiner Signature	<i>calombie</i>	Date Considered	6.30.05
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*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.

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CL		5,808,318		Masumo et al.	09/15/1998	—
		5,904,550		Yamaguchi	05/18/1999	—
		5,773,309		Weiner	06/30/1998	—
		5,851,860		Makita et al.	12/22/1998	—
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		5,387,309		Bobel et al.	02/07/1995	—
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CL		JP	05-243576			09/21/1993	— Abst.
CL		JP	08-051078			02/20/1996	— Abst.
CL		JP	06-204132			07/22/1994	— Abst.

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CL		F. Ueno "Observation of fast microscopic phase change phenomena of chalcogenide thin films," Japanese Journal of Applied Physics, Supplement, Vol. 26, Supplement 26-4, pp. 55-60, 1987.	
CL		N. Kondo et al., "Film thickness measurement of ultrathin film using light of UV wavelength," Proceedings of the SPIE, Vol. 1673, pp. 392-402, 1992.	

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CL		5,503,707		Maung et al.	04/02/1996
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CL		C. Hayzelden et al., "In Situ Transmission Electron Microscopy Studies of Silicide-Mediated Crystallization of Amorphous Silicon," (3 pages) Appl. Phys. Lett. 60(2) pp. 225-227, 1/1992.	
CL		A.V. Dvurechenskii et al., "Transport Phenomena in Amorphous Silicon Doped by Ion Implantation of 3d Metals," USSR, pp. 635-640, Phys. Stat. Sol. (A) Vol. 95, 1986.	
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